Notice of Allowability	Application No.	Applicant(s)	
	10/711 145	10/711,145 CHEN ET AL.	
	Examiner	Art Unit	
	Brook Kebede	2823	
The MAILING DATE of this communication applied allowable, PROSECUTION ON THE MERITS therewith (or previously mailed), a Notice of Allowance (PTOL-NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.5	IS (OR REMAINS) CLOSED in 85) or other appropriate comm relights. This application is:	n this application. If not includ unication will be mailed in due	ed course. THIS
1. X This communication is responsive to the RCE filed on J	lanuary 16, 2007.		
2. X The allowed claim(s) is/are 1,4,5,9-11 and 13.	•		
 Acknowledgment is made of a claim for foreign priority a)	ave been received. ave been received in Application	on No	ation from the
Applicant has THREE MONTHS FROM THE "MAILING DAT noted below. Failure to timely comply will result in ABANDO THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the re	quirements
4. A SUBSTITUTE OATH OR DECLARATION must be su INFORMAL PATENT APPLICATION (PTO-152) which (NOTICE OF
 5. CORRECTED DRAWINGS (as "replacement sheets") replacement sheets") replacement sheets. (a) including changes required by the Notice of Draftsperior 1) hereto or 2) to Paper No./Mail Date	person's Patent Drawing Reviews er's Amendment / Comment of R 1.84(c)) should be written on the header according to 37 Claposit of BIOLOGICAL MAT	r in the Office action of the drawings in the front (not the FR 1.121(d). ERIAL must be submitted.	·
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-94) 3. ☐ Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date 4. ☐ Examiner's Comment Regarding Requirement for Depose of Biological Material 	8) 6. 🖾 Interview S Paper No. 7. 🖾 Examiner's	Informal Patent Application Summary (PTO-413), Mail Date Amendment/Comment Statement of Reasons for Alle BROOK KEBEDE PRIMARY EXAMIN	'ebede

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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on January 16, 2007 has been entered.

EXAMINER'S AMENDMENT

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mr. Howard M. Cohn on March 27, 2007.

3. The application has been amended as follows:

In the Claims:

Change claim 1 to --Method of forming an interconnect structure comprising the steps of:

depositing a dielectric layer of ultra low-k material; forming a hard mask over the <u>dielectric</u>

layer, wherein the hard mask comprises: a layer of silicon carbide (SiC) material including

(SiCOH) material overlying the dielectric layer; and a layer of oxide material overlying the silicon carbide material; etching trenches in the dielectric <u>layer</u>; depositing a liner over the hard

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mask and within the trenches; and overfilling the trenches with a conductive material; performing a chemical mechanical polishing process to remove the conductive material which is atop the liner, thereby exposing the liner; removing the portion of the liner which is atop the hard mask using a Gas Cluster Ion Beam (GCIB), leaving the conductive material protruding from the trenches; and removing the layer of oxide material using a wet etch process, leaving the layer of silicon carbide material, the conductive material and the liner material above the layer of silicon carbide material protruding from the trenches; and performing a touch-up polishing process to remove the conductive material and the liner protruding from the trenches.--.

Change claim 9 to -- The method of claim 1, further comprising the step of: ensuring that the layer of oxide material is thick enough such that topographical variations after the chemical mechanical polishing process and the removal of the liner are entirely within the layer of oxide material of the hard mask.--.

Change claim 13 -- The method of claim 1, wherein the touch-up polishing process comprises using an abrasive-free or low-abrasive polish to obtain a very high selectivity between the conductive material and the silicon carbide material of the hard mask.--.

Allowable Subject Matter

Claims 1, 4, 5, 9-11 and 13 are allowed over prior art of record. 4.

Reasons for Allowance

5. The following is an examiner's statement of reasons for allowance: Art Unit: 2823

After further search and consideration of the amendment filed on November 14, 2006, it is determined that The prior art of record neither anticipates nor renders obvious the claimed subject matter of the instant application as a whole either taken alone or in combination, in particular, prior art of record does not teach "removing the portion of the liner which is atop the hard mask using a Gas Cluster Ion Beam (GCIB), leaving the conductive material protruding from the trenches; and removing the layer of oxide material using a wet etch process, leaving the layer of silicon carbide material, the conductive material and the liner material above the layer of silicon carbide material protruding from the trenches; and performing a touch-up polishing process to remove the conductive material and the liner protruding from the trenches," as recited in claim 1.

Claims 4, 5, 9-11 and 13 are also allowed as being dependent of the allowed independent base claim.

Conclusion

- 6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure Dalton et al. (US 2002/0074659), Chen et al. (US 2002/0182853) and Choi et al. (US 6,486,082) also disclose similar inventive subject matter. However, the prior art neither teaches nor renders obvious the aforementioned claimed limitations of the instant application either taken alone or in combination.
- 7. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Correspondence

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Brook Kebede whose telephone number is (571) 272-1862. The examiner can normally be reached on 8-5 Monday to Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (571) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Brook Kebede Primary Examiner Art Unit 2823

BK March 29, 2007